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Hand-drawn diagram illustrating a diffraction pattern. The top part shows a series of peaks labeled with 2θ values: 208, 224, 228, 204, 232, 216, 236, and 220. The bottom part shows a rectangular block with a central horizontal line and a label 124 pointing to it.

A cross-sectional view of a semiconductor device. A substrate 304 is at the bottom. Above it is a layer 308. On top of layer 308 are three stacked structures. The first structure on the left is labeled 312. The middle structure is labeled 316. The rightmost structure is labeled 320. Each of these structures (312, 316, 320) consists of a base layer and a top layer with a wavy, undulating surface profile.

Figure 3

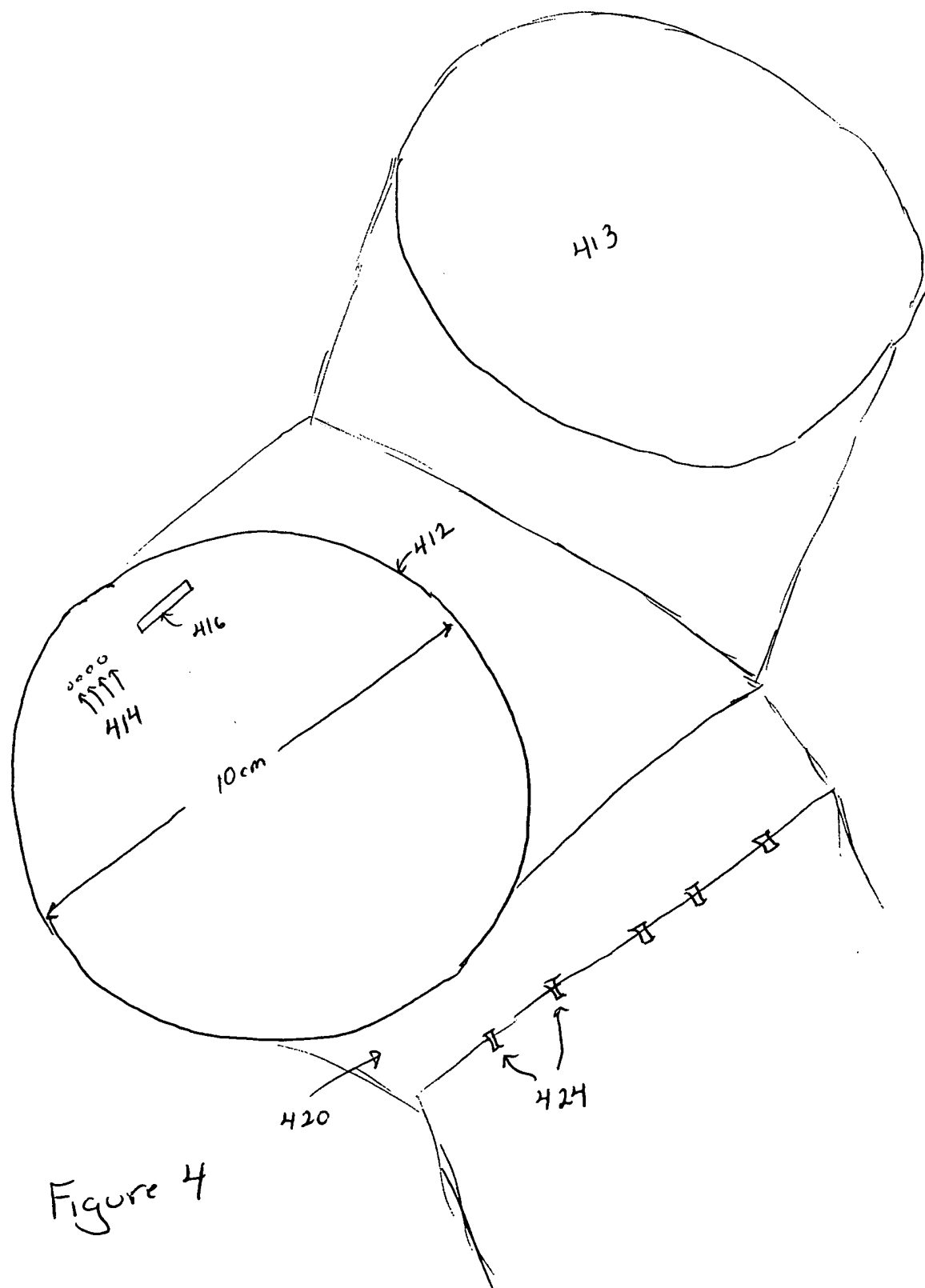
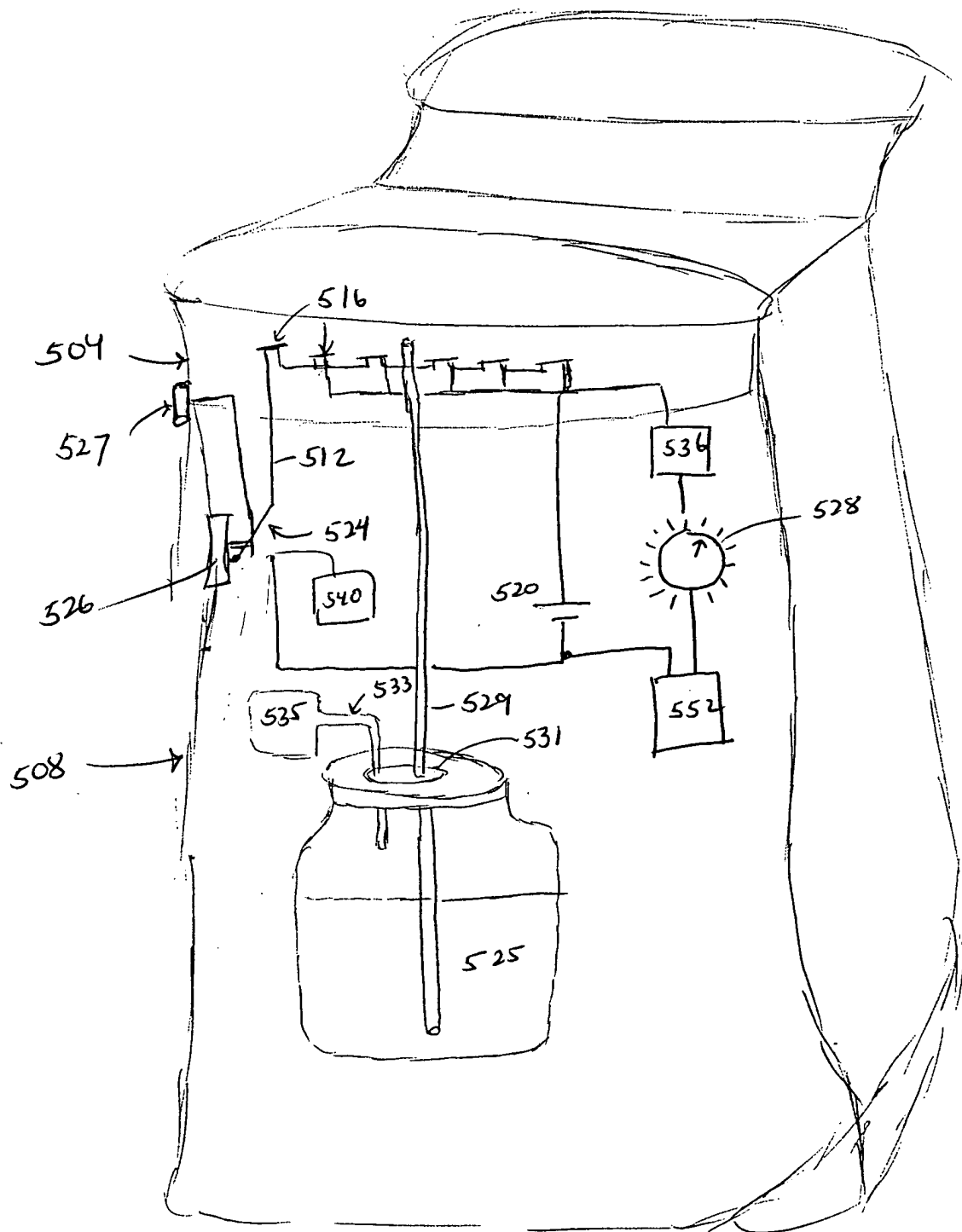
[illegible]

Figure 4

Figure 5



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Figure 6

